Flat-B and Ferrom agnetism in Organic Polymers Designed by a Computer Simulation

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By coupling a rst-principles, spin-density functional calculation with an exact diagonalization study of the H ubbard m odel, we have searched over various functional groups for the best case for the at-band ferrom agnetism proposed by R.Arita et al. Phys. Rev. Lett. 88, 127202 (2002)] in organic polymers of vermem bered rings. The original proposal (poly-am inotriazole) has turned out to be the best case am ong the m aterials exam ined, where the reason why this is so is identied here. We have also found that the ferrom agnetism, originally proposed for the half-lled at band, is stable even when the band lling is varied away from the half-lling. All these make the ferrom agnetism proposed here more experimentally inviting.

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I. IN TRODUCTION

M aterials design to realize desired properties in condensed-m atter physics is becoming increasingly realistic. One important factor is, given high levels of computer performance, the computer simulation is an essential part in designing. Namely, computer simulations with rst principles calculations should be imperative in narrowing down, or even pin-point, from a wide variety of candidate or designed m aterials for the interesting properties and functions we search for. Such an approach is especially promising form olecules and nanostructures. W hile the atom manipulation with scanning tunneling microscopy (STM)^{1,2,3,4} provides new possibilities for materials design, the design of molecules, especially polymers as we focus on here, should be fundam ental.

In this context organic molecules and polymers are of special interest, since they have versatile structures and chemical properties that can be wider than in inorganic materials. Indeed, the discovery of a conducting organic polymer by Shirakawa^{5,6} kicked o intensive studies that are paving a new way to adopt organic polymers or oligomers in realizing various functions as molecular-electronics devices such as eld-e ect transistors⁷ or light-emitting diodes⁸.

O rganic ferrom agnets have also attracted much attention as a challenging target^{9,10}. In particular, organic magnets consisting entirely of non-magnetic elements is of fundamental as well as practical interests. O rdinary ferrom agnets consisting of magnetic elements exploit electrons in d-or f-orbitals that are strongly interacting. C an magnetism arise in p-electron systems that are weakly interacting? O ne theoretical possibility is to apply the at-band ferrom agnetism proposed by M ielke and by Tasak i^{11,12}. This arises as an elect of electron-electron repulsion when the (one-electron) band structure contains a dispersionless band. The mechanism is interesting in many ways, but essential features are, rst, the system is totally distinct from the \narrow-band lim it" in

textbooks, since the magnetism occurs when the transfer between di erent sites is nite.

Second, this is a band ferrom agnetism rather than a m agnetism arising from the exchange interaction between localized spins. So, thism echanism should be a good candidate for designing organic ferrom agnets. W hile there are also other possible m echanism s such as the intram olecular H und's coupling for spins in p-orbitals⁹, the at band ferrom agnetism is advantageous in that spins are carried by itinerant electrons which can be utilized for spin in jectors in spintronics.

Here a theoretical remark on the at-band ferrom agnetism is due. The at-band ferrom agnetism was rst proposed by Lieb,¹³ who considers bipartite lattices (consisting of two sublattices) that have di erent num bers of A sublattice sites N $_{\rm A}$ and B sublattice sites N $_{\rm B}$. Lieb proved that, when we switch on the electron-electron repulsion (assumed to be short-ranged, so that we take the Hubbard model), the ground state should then be ferrim agnetic with the magnetization / N_A N_B.Quantum chemically, this model contains N_A N_B nonbonding molecular orbitals, so is similar to Mataga's model. Shim a and Aoki¹⁴ then proposed a system atic way to realize such systems as superhoneycomb structures. Mielke^{15,16,17} and independently Tasaki¹⁸ then constructed other at-band ferrom agnetism, which is distinct from Lieb's in that the at band is constructed from quantum mechanical interference between the nearestneighbor and further transfers (so the system is necessarily non-bipartite) and the ground state is now ferrom agnetic.

To be more precise, the lattice is required to satisfy what is called the \local connectivity condition". Namely, the at band is by no means a su cient condition for ferrom agnetism, and the magnetism arises for special lattices on which adjacent \W annier" orbitals have to overlap with each other no matter how they are com bined to minim ize each orbit size. So, while ordinarily a at band im plies a disjointed set of orbits, they are connected in M ielke-Tasaki lattices. This is intuitively why spins align to lower the repulsion energy from Pauli's principle. Rigorous proof for the ferrom agnetic ground state has been given for the half-led at band.

In actual materials, it is very hard to realize perfectly at bands, and to make them perfectly half-led. For the form er, a rigorous proof (for M ielke-Tasaki lattice)¹⁹ and num erical sim ulations^{20,21} show ed that a slight band dispersion does not destroy the magnetism. For the latter, there are also a proof⁴¹ and a num erical sim ulation²⁰ which revealed that sm all deviations from half-lling are allow able for the ferrom agnetism .

In the context of this background, what kind of organic materials are promising for realization of the atband ferrom agnetism? The hardest part is to realize the connectivity condition. In general we have to consider com plex lattices such as K agom e, or lattices having distant-neighbor transfers. However, the condition is easier to satisfy on one-dimensional polymers. For exam ple, M ielke-Tasaki m odel is realized as a chain of triangles.^{20,22,23} So we can concentrate on polymers.

N ext com es the choice of the m onom ers that should be polym erized. Even-m em bered rings such as benzene are disadvantageous in that antiferrom agnetic order tends to occur, which should dom inate over the ferrom agnetism . So we should opt for odd-m em bered rings, and the above exam ple of the chain of triangles is indeed an exam ple of this. Since triangular m olecules are scarce, we can conclude that we should focus on polym ers based on vem em bered rings, such as polypyrrole, polythiophen, etc.

For the computer design, the purpose of the present paper, there are two tasks: (i) to search for the materials that realize the at band a la M ielke-Tasaki. Since the chain of odd-m embered rings is by no means a su cient (nor necessary) condition for the at band, this is an important part.

(ii) Next, we should do a rst-principles (spin density functional) band calculations to con rm (a) the atness of the band and the ferrom agnetism in the ground state, and (b) whether them agnetism can indeed be interpreted as the M ielke-Tasaki mechanism, for which we have to evoke an electron-correlation calculation (exact diagonalization of the H ubbard m odel here). (c) W e also address the question of how the departure from half-lling a ects the m agnetism in the at band.

For the rst-principles calculation, we have employed the generalized gradient approximation²⁴ (GGA). Depending on the purpose of each calculation, we have performed either the spin-unpolarized case based on the density functional theory (GGA-DFT) or the spin-polarized one based on the spin density functional theory (GGA-SDFT). We used the plane-wave-based ultrasoft pseudopotentials^{25,26}. The energy cuto was taken as 20.25 Rydberg. The convergence criterion of the geometry optimization was that all of the forces acting on each atom were within 1 10 ³ Hartree/au.

The plan of this paper is as follows. In section II, we describe the search for various materials and show some examples which exhibit possibilities of ferrom agnetism.

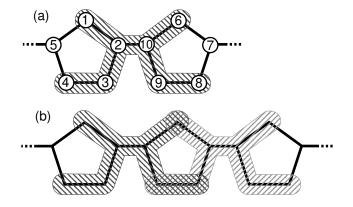


FIG.1: Schem atic view of (a) the eigenfunction that satis es the connectivity condition and (b) the overlap of the adjacent eigenfunctions.

In section III, we show the result for the most prom ising material, poly-am inotriazole, and discuss how the theory for the at-band ferrom agnetism works on this particular material. In section IV, we discuss how the ferrom agnetic state is robust against the deviation of the band lling from the half-lling.

II. EXAM INED MATERIALS

A. Flat bands in the polymer of ve-membered rings

Let us rst exam ine the sim ple tight-binding m odel,

$$H = \begin{array}{ccc} X & X^5 \\ H = t & c_1^y c_j + "_0 & n_i + "_1 n_1; \\ & & & & \\ & & & & & \\ & & & & & i=2 \end{array}$$

for a chain of ve-m em bered rings, where we rst assume that all the transfer integrals within the ring and those connecting rings have the same t, all the on-site energies are the same ($"_0 = 0$), except for the one at the top of the ring ($"_1$). We rst consider the half-lled case where one electron per site on average. This is a reasonable assumption when we consider -orbital networks on such polym ers.

Let us start from an observation that M ielke-Tasaki's condition is satis ed when " $_1 = t (> 0)$, a not unrealistic condition. In this case, the third band with E = 0, i.e., the half-led band, has no dispersion. This provides a heuristic example for the M ielke-Tasaki eigenfunctions: one can construct the most com pact eigenfunction which consists of two rings as depicted in F ig. 1(a), where the am plitudes of the numbered sites are given as (1, 1, 0, -1, 0, -1, 0, 1, 0, -1). The fact that the am plitudes at the sites 5 and 7 are zero ensures the localized nature of this eigenfunction. Note that we are not displaying a part of a B loch function, but the whole eigenfunction. O ne can

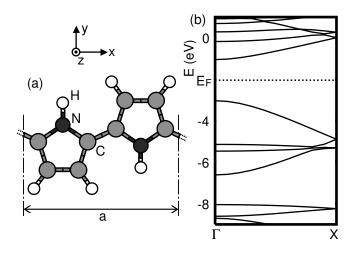


FIG.2: (a) An atom ic structure of polypyrrole. The structure extends along the right and left directions periodically. (b) The (GGA-DFT) band structure of polypyrrole.

also construct another, linearly-independent eigenfunction by simply shifting the wave function from one ring to the next. The eigenvalue of the new function is the same (E = 0). So the set of all these eigenfunctions can be a basis for the at band. Because the eigenfunction is not con ned in a single ring (unit cell) but extends over the two rings, two neighboring bases (eigenfunctions) always overlap with each other as shown in Fig.1 (b). One cannot rem ove such overlaps between the bases are taken. This overlap is the origin of the ferrom agnetic coupling between the electrons in the at band.

B. Known polymers of ve-membered rings

A typical polymer of vermembered rings is polypyrrole. The atom is structure and calculated band structures are shown in Figs. 2(a) and (b), respectively. The vermembered rings alternate their directions in this compound, so that the unit cell contains two rings. X point in Fig. 2(b) has k = (=a;0;0), where a is the lattice constant of this unit cell as shown in Fig. 2(a). Because of the doubled unit cell, most of the bands are folded at X. For directions (y;z) perpendicular to the chain, we have taken a cell size large enough to avoid inter-chain interactions. We can see that polypyrrole has, not surprisingly, no at bands around the Ferm interaction.

We have also boked at other typical polymers of vemembered rings, including polythiophen (where an N-H block in polypyrrole is replaced with an S atom) and polytriazole (where all the C-H blocks in polypyrrole are replaced with N atom s). However, their band structures have no at bands, either.

${\tt C}$. ${\tt D}$ esigning the polymer

This is exactly where the designing comes in. Our strategy consists of two approaches. One is to replace H atom bound to N atom at the top of the ring with various kinds of bases. A coording to the tight-binding calculation described in the previous subsection, the onsite energy $("_1)$ of the top of the ring should be higher than that of C atoms to have a at band. Because the on-site energy of N is expected to be lower than that of C, the rst attempt should be the replacement of the N atom with other elements with higher on-site energies. However, that should be di cult if one wants to retain the existence of the -orbital and single electron occupation on it. Therefore, we have opted for controlling the on-site energy by replacing the H atom with other functional groups, by leaving the N atom intact.

A lternatively, we can replace C-H blocks on the bottom edge of the pentagons (3, 4, 8, 9 in F ig.1(a)) with N atom s, where the lowering of the on-site energies of the bottom of the ring may e ectively realize the required condition. In other words, we use polypyrrole and polytriazole as the platform to modify either the top or the bottom of the ring. Since it is not obvious which approach should be better, we consider both platform s for all the substituents considered here.

Substituents we have tested are sodium (Na), potassium (K), chlorine (Cl), uorine (F), cyanogen (CN), nitro (NO₂), sulfate (SO₄), carboxyl (COOH), am ino (NH₂), methyl (CH₃), and hydroxyl (OH). For all these candidates, we have performed rst-principles (GGA-DFT) optimization of atom ic structures, and obtained their band structures. Most of them have no at bands around E_F , but some of them have turned out to have at bands. For these we have perform ed further (GGA-SDFT) rst-principles optimizations under the doping condition to make the at band half-led.

First, we have exam ined single atom s (alkalim etal or halogen) as substituents. This is motivated by the fact that small substituents may be better than larger ones, because a bulky group at the top of the ring may introduce a coupling (transfer) with the bottom of the adjacent ring, which would destroy the basic assumption that the adjacent rings are connected by one bond to satisfy M ielke-Tasaki's condition.

In order to raise the on-site energy of the top of the ring, we have rst considered an alkalim etal atom, N a, because of its low electron a nity. Figure 3 (a) shows the atom ic structure of poly-sodium -triazole, where hydrogen atoms in polytriazole are replaced by sodium atoms. Figure 3 (b) shows the band structure, where one can see that a nearly at band exists above the Ferm i energy. A beence of any unnecessary bands between the at band and E_F is good sign, because we can dope carriers into the at band without any com plications.

We have also exam ined the Na-substituted polypyrrole, and obtained a sim ilar band structure. However, in this case the at band above E $_{\rm F}$ is much closer to a dis-

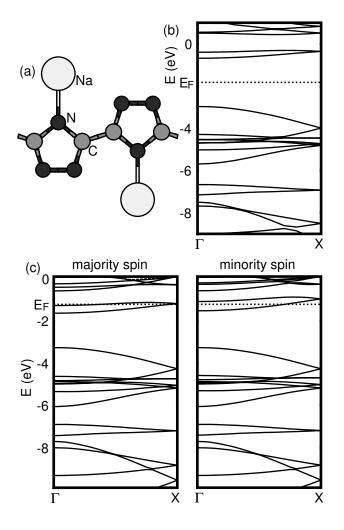


FIG. 3: (a) The optim ized atom ic structure of poly-sodium - triazole, the band structure of poly-sodium -triazole when undoped (spin unpolarized) (b), and doped (spin polarized) (c).

persive band below E $_{\rm F}$, which can introduce unwanted inter-band interactions. As for the alkalim etal we have also considered potassium, but the case of N a has turned out to be better.

W emove on to the doping. First, the at bands always appear as a pair of bands folded at X point, except for the case of antiferrom agnetic ordering. Therefore, we make the at-band half-led by doping two carriers per unit cell into the pair of at-bands. N am ely, one carrier is doped for each ring. In poly-sodium -triazole, we have considered the doping of two electrons per unit-cell. Here we realize the doping condition by increasing the num ber of electrons with a uniform positive background charge for charge neutrality.

A fler a geometrical optimization of doped polysodium-triazole, we have calculated the spin-dependent (GGA-SDFT) band structure in Fig. 3(c). One can see that the number of occupied states di ersbetween majorand m inor-spins, which means that the system is ferrom agnetic. It should be noted that (the pair of) the at band is not entirely spin-split. The di erence of the num ber of spins is 0.65 per unit cell. The spin polarization is smaller than the expected polarization (2.0). We also found that the total energy (per unit cell throughout this paper) of the ferrom agnetic (F) state is lower by 12 m eV than that of the param agnetic (P) state. We could not nd antiferrom agnetic (AF) solution even when we started geometry optimization from an AF electronic state. So the F state is the most stable in this material, but is only slightly lower in energy than the P state.

The reason why this material gives such an insu cient result in spite of the existence of the nearly at band should be sought in the nature of the at-band's wave function. We found that the half-lled at band here is made of an orbital localized around the N a atom, so does not satisfy the local connectivity condition. This should be why the stability of the F state is very weak, while the nite spin-polarization in GGA-SDFT should be a narrow-band e ect rather than a much more robust M ielke-Tasakie ect. Indeed, the di erence between the weak ferrom agnetism here and a robust ferrom agnetism in poly-am inotriazole, show n later, is a good dem onstration of the im portance of the local connectivity condition, hallm ark of the at band ferrom agnetism .

Now we digress a bit, and consider the contrary case of an atom having high electron a nity such as a halogen, e.g., uorine atom, which m ight be heuristic. Figure 4 (a) shows the atom ic structure of poly- uoropyrrole, where the uorine atoms are substituted for hydrogen atoms bound to nitrogen atoms in polypyrrole. Figure 4 (b) is the band structure obtained by spin-unpolarized (G G A – D FT) calculation. We nd a at band which lies just in between two dispersive bands below E_F . Because of this the doping greater than one carrier per unit cell is required.

So we consider making the at-band half-lled by doping four holes per unit-cell. Here, two holes are necessary to make the dispersive band just below the Ferm i level empty, and two holes are necessary to make the folded at bands half-lled. Figure 4 (c) shows spin-dependent band structure after the geom etry optim ization under the doping condition. The system is seen to be ferrom agnetic. The di erence of the num ber of spins per unit cell is just 2.0. One problem of this material, however, is that doping twice as large is necessary. W hen the doping is performed in this material, the at band shifts upward (downward) for minority (majority) spin. Replacing the uorine atom with a chlorine atom results in a band structure sim ilar to the case of uorine. In fact an AF state, obtained by starting geometry optimization from an antiferrom agnetic state, has a total energy 21 meV lower than that of F state.

W e move on to functional groups as substituents to search further possibilities. W e have considered an example, poly-hydroxytriazole, where H atom in polytriazole is replaced by OH with a low electron a nity. A lthough a pair of slightly dispersive bands exist just below E_F , these bands, when doped with two holes per unit cell,

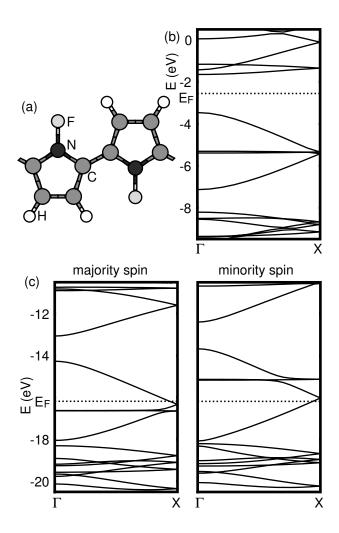


FIG. 4: (a) The optimized atomic structure of polyuoropyrrole, the band structure of poly-uoropyrrole when undoped (spin unpolarized) (b), and doped (spin polarized) (c).

become m ixed with dispersive bands underneath. As a result, the di erence of the number of spins in the F state is only 0.39 per unit cell, and the paramagnetic state is m ore stable than the F state by 3 m eV.

Figure 5(a) is the atom ic structure of polyaminopyrrole, where H atom bound to N atom in polypyrrole is replaced by NH_2 , whose electron a nity is low. In the band structure, Fig. 5(b), one can nd a pair of at bands below E_F . The lower half of it is very at while upper half is slightly dispersive.

We have then doped two holes per unit cell. The band structure after geometry optimization is shown in Fig.5(c). The dimension of the number of spins is 1.0 per unit cell. As one can see from Fig.5(c), the Fermi level intersects the middle of the pair of at bands. Although the lower part of the pair of at bands is quite at, the dispersion of the upper half part is too large. Here only lower half part seems to work as a at-band. The total energy of param agnetic state in this material is found to

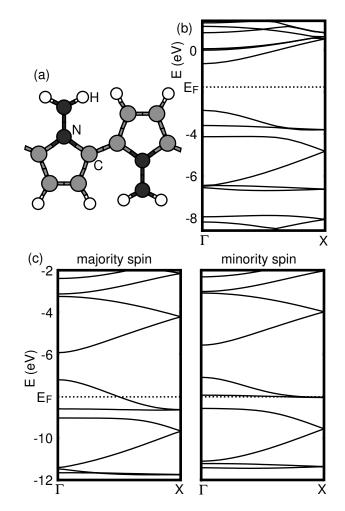


FIG. 5: (a) The optimized atom ic structure of polyam inopyrrole, the band structure of poly-am inopyrrole when undoped (spin unpolarized) (b), or doped (spin polarized) (c).

be 65 m eV higher than that of ferrom agnetic state, while an AF solution does not exist, so the F state is the m ost stable.

A llother substituents tested here except for the one in the next section have turned out to be inappropriate. In m ost of those m aterials, the band which we expect to be at is either too dispersive or too deep. For the rem aining ones, band structures are qualitatively sim ilar to the exam ples described in this section. Poly-am inotriazole, discussed in the next section, also gives qualitatively sim ilar results to poly-am inopyrrole shown in this section, but quantitatively m uch better.

III. POLY-AM INOTRIAZOLE

A. First principles calculation

The best candidate for ferrom agnetic organic polymer among the materials we have considered is poly-

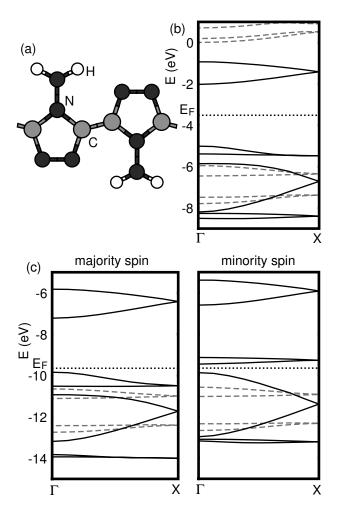


FIG. 6: (a) The optimized atom ic structure of polyam inotriazole, the band structure when undoped (spin unpolarized) (b), and doped (spin polarized) (c). The bands having () character are shown by solid (dashed) lines, respectively.

am inotriazole²⁷. Figure 6(a) shows the atom ic structure of poly-am inotriazole, where H atom in polytriazole is replaced with NH_2 . The di erence between polyam inopyrrole shown in the last section and this material iswhether the platform ispolypyrrole or polytriazole, i.e., the C-H blocks in the bottom of the ring is replaced with N atom s. The band structure of the poly-am inotriazole, shown in Fig. 6(b), is sim ilar to that of Fig. 5(b), but the dispersion of the upper half of the pair of at bands is smaller and the separation from dispersive bands below is greater than that of Fig. 5(b). These features are desirable for the at-band ferrom agnetism.

A fler the optim ization of the atom ic structure under the doping condition of two holes per unit cell, the spin dependent band structure was calculated and shown in Fig. 6 (c). The result hits on the ideal situation | The pair of at bands is made half-led, and as a result, fully occupied by majority spins while totally unoccupied by minority spins. Rejecting this situation the difference of

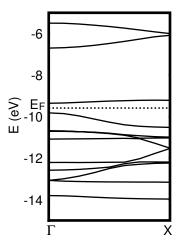


FIG. 7: A band structure for a m etastable antiferrom agnetic state in poly-am inotriazole.

the number of spins is the desired 2.0 per unit cell.

In this material, we found a metastable antiferrom agnetic state. The band structure of the AF state is shown in Fig. 7. This is calculated with GGA-SDFT, but the resulting band structures for up- and down-spins are the same, while the wave functions for up- and down-spins are arranged alternately on the chain of rings. This means that even though we have avoided intra-ring AF instability by choosing ve membered rings, inter-ring AF can exist at least as a metastable state. The upper and low erparts of the at band folded at X point is separated with $E_{\rm F}$ in between. The AF state is found to be 52 m eV higher in energy than the F state. Param agnetic state is even higher (by 384 m eV) than the F state.

Let us discuss how the at-band ferrom agnetism is achieved in this material by combining the wave functions of the at band obtained by rst principles calculation with the calculation in the tight-binding model. Figure 8 shows the majority-spin's wave functions in the pair of at bands just below the Ferm i level in Fig. 6(c). W hile the phases of the wave functions can be taken arbitrarily, we choose for clarity the wave functions of the lower and upper bands at point (Figs. 8(a) and (f)) to be real and pure in aginary, respectively, and those at interm ediate k-points to be continuous. If we rst look at the realpart, typically for Fig. 8 (a), the wave function for each monomer (am inotriazole) has two nodal lines which divide the amplitude into three parts, corresponding to NH₂, C-N-C, and N-N blocks. For the imaginary part, typically for Fig. 8(f), the wave function has one nodal line, which divides the amplitude into two, consisting of two C-N blocks. The two wave functions (real and im aginary), which are orthogonal, are mixed at the interm ediate k-points.

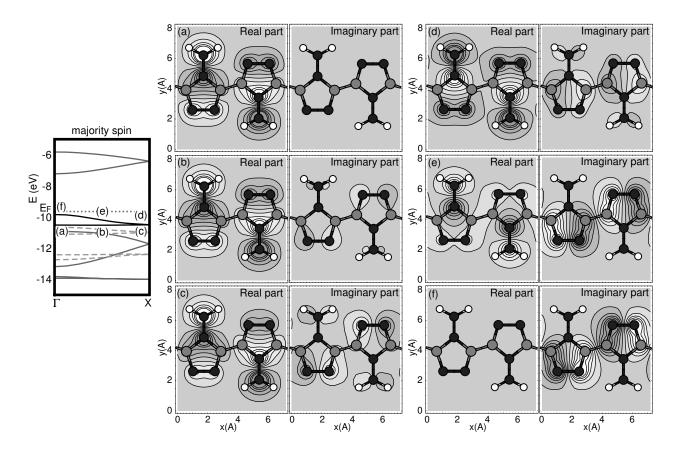


FIG. 8: W ave functions of the polarized lower band (a, b, c) and upper band (d, e, f) of poly-am inotriazole. (a, f) for $k_x = 0$ (), (b, e) for $k_x = -2a$, and (c, d) for $k_x = -a$ (X). Inset at the left side indicates the band and k-point of each gure.

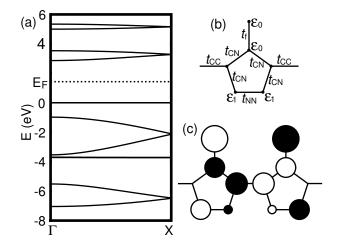


FIG.9: (a) Band structure in the tight-binding model. (b) Tight-binding parameters used for the tting. (c) The eigenfunction which satis as the connectivity condition.

B. Tight-binding model

In order to capture the essence of the % = 1 that, here we introduce a tight-binding model which represents – orbital's network in this system . Figure 9(a) shows its band structure. The parameters of the model displayed in Fig.9(b) are tted so as to reproduce Fig.6(b). Obtained values are: $t_{\rm C\,N}$ = $t_{\rm C\,C}$ = $t_{\rm f}$ = 2.5 eV, $t_{\rm N\,N}$ = 3 eV, $"_0$ = 1.4 eV, and $"_1$ = 0.5 eV. One can see that the tight-binding band (Fig.9(a)) excellently agrees with the -bands obtained by rst-principles calculation (solid lines in Fig.6(b)).

Figure 9(c) shows the tight-binding wave function of the eigenstate corresponding to that in Fig.1(a). In this material, one site is added to the top of the ring which represents a nitrogen atom of NH₂. The open and closed circles indicate the sign of the wave function, respectively, and their sizes am plitudes. This wave function satis es the local connectivity condition.

Here it should be noted that the substitution of NH_2 for H not only raises the on-site energy of the top of the ring but also introduces an extra -orbital of the N in NH_2 . The existence of the extra site completely changes the connectivity condition, so that we have no longer to satisfy "₁ = t > 0, which has turned out in the present

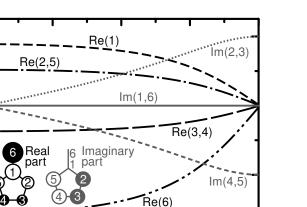


FIG.10: $k\mbox{-dependence}$ of the wave functions in the tight-binding model.

X(π/a)

study to be rather di cult condition to realize.

0.5

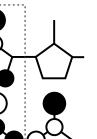
0

Amplitude

-0.5

Figure 10 shows k-dependence of the tight-binding wave functions of the at band. Here k-space is extended to the second B rillouin zone, so the left and right halves of the gure represent the wave functions of the low er and upper parts of the pair of at bands, respectively. P hase factors are chosen again for clarity as in Fig. 8. The label Re(2,5)" indicates that the line represents the real part of the wave function at the site 2 and 5, where the num bering of the sites is shown in the insets. On the – points at the left- and right-edge of the gure, the wave function becomes real and pure in aginary, respectively. These two wave functions are displayed in the inset of Fig. 10, where it should be noted that we display a part of the periodically extending B loch functions, in contrast to Fig. 9(c) which shows the entire eigenfunction.

One can see that the symmetry and the character of the wave functions shown in Fig. 10 is similar to the rst-principles wave function (Fig. 8). These wave functions can be constructed by a linear combination of the eigenfunctions shown in Fig. 9(c). Figure 11 illustrates how the linear combination of the localized eigenfunctions provides the B loch function. W hen the two neighboring eigenfunctions, A and B, are added, the sum at the ring on which they overlap (enclosed by dotted lines) form s the shape of the imaginary-part wave function as shown in the inset of Fig.10. When subtracted, it forms the shape of the real-part wave function. The entire in aginary-and real-part wave functions are constructed by the sum mation of all localized eigenfunctions (A + B + C + D +summation and subtraction (A B + C D +tively. The real-part wave function and the imaginarypart wave function are orthogonal to each other. The gradual mixing of these two orthogonal wave functions ask is changed is the very character of the Mielke-Tasaki at band, which should never occur on an ordinary at



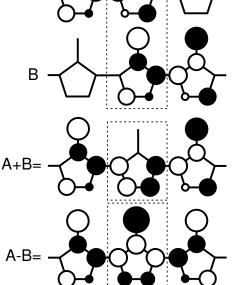


FIG. 11: Schem atical linear combinations of the neighboring eigenfunctions.

band.

Γ(2π/a)

C. Comparison with the Hubbard model

Having constructed the tight-binding modeling we proceed to the question of whether the ground state is spin-polarized pin the presence of the Hubbard interaction, $H_U = U_{i} n_{i^{m}} n_{i^{\#}}$. In Fig. 12 we show the phase diagram against U and "1 obtained with an exact diagonalization calculation for a 12-site (2 rings) Hubbard model for $t_0 = 2.5$ eV and various values of $t_{NN} = 3.0$ 4.0 eV. As indicated in the inset, "0 is chosen throughout to satisfy the condition for the at band,

$$\label{eq:transform} \begin{array}{cccc} & & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & & & \\ & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & &$$

d real-part wave functions where " is the eigenenergy of the at band and $t_{CN} = t_{CC} = t_0 (= 1 \text{ here})$ is assumed for sim plicity. We can) and the combination of the see that we have indeed a ferrom agnetic phase unless the A B+C D+), respec-repulsion is too strong (i.e., U < U_c with U_c = 2 5 eV). Our prelim inary quantum M onte C arb calculation conm s that two unit cell is su cient to roughly determ ine the ferrom agnetic phase boundary. Peculiar destruction of the ferrom agnetism above U > U_c is another hallm ark of the M ielke-Tasaki m agnetism.²¹

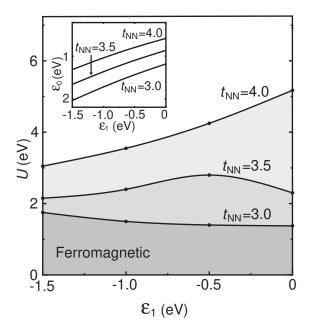


FIG. 12: Stability of the ferrom agnetic phase calculated with an exact diagonalization of the Hubbard model.

IV. DEVIATION FROM THE HALF-FILLED FLAT BAND

A. Com parison of the total energies

In order to realize ferrom agnetism in the materials we proposed here, carriers have to be doped into the at band. We can consider several possible methods to achieve this such as eld e ect doping²⁸, photo-induced carrier injection²⁹, as well as chemical doping. The rst two are now attracting much attention in molecular electronics, but they are very recent techniques and may need further developments. We can instead concentrate on the chemical doping, where the polymers are crystallized along with the accepters, and we found it feasible. Details are presented elsewhere³⁰. Now, if the at-band ferrom agnetism can occur not only just at the half-lling but also away from that, this would make the chemical doping much easier.

W e have to know how robustly the ferrom agnetism survives when the lling of the at band deviates from just half-lled. A lthough there is a proof¹¹ and a num erical study²⁰ for a M ielke-Tasaki lattice which show that slight deviations do not wash out the ferrom agnetism, those conclusions m ay not be simply applied to other m odels. For the present m odel, calculations taking full account of the electronic correlation such as the exact diagonalization of the H ubbard m odelw ould be unsuitable, because changing the num ber of electrons in sm all systems corresponds to too big a change in the lling. We have instead perform ed an SD FT calculation, because it can handle the fractional num ber of electrons (per unit

cell) if a uniform background charge is introduced.

At this point we can note the following. In SDFT calculations, electronic correlations are not fully taken into account, so we can question whether the at band ferrom agnetism may be described within the SDFT fram ework. This problem has been addressed in our previous publication²⁷ where SDFT and exact diagonalization of a Hubbard model have given qualitatively consistent results. This is not surprising, since one of the remarkable features of the at-band ferrom agnetism is that the magnetism exists over the whole range (in nitesimal < U < 1) of the interaction as proved rigorously, so the weak-U case (for which the methods such as SDFT is meant to be applicable) crosses continuously over to strong-U case. As far as the on-site repulsion is not too strong, the com parison between the gain of the exchangecorrelation energy by spin polarization (F state) and the gain of the band energy by form ing AF order (or equivalently, a spin density wave (SDW) with the periodicity of two ve-m em bered rings) accompanied by a lattice relaxation should predom inantly determ ine which state is stable. These two energies can be accurately estimated by SDFT calculations. Therefore, we expect here that SDFT can serve our purpose, to see the band-lling dependence of the total energies of F, AF, and P states.

Figure 13 (a) shows band-lling dependence of the total energies of the F and AF states of the polyam inotriazole measured from that of the P state. The position where the number of holes, n_h, is 2.0 corresponds to the half-lling. The results for F, AF, and P are obtained by fully relaxing the atom ic geometry for each electronic state. It can be seen that F state is stable in the range $1:1 < n_h$ 2:0, while P state is stable for $n_h < 1:1$. In the region where F is stable, AF is found to be metastable. In the P-region, $n_h < 1:1$, no AF state is found. This result shows that the ferrom agnetism in this material is robust, even down to the quarter lling, against the deviation from the half-lling. The result that quarter-lling is acceptable greatly relaxes the di culty in doping.

B. Correlation with the atom ic con guration

Since the polym er proposed here has functional groups, we should also exam ine how the three-dimensional atom ic con guration is correlated with the band-lling dependence. Namely, all the atom s do not lie on a plane: in poly-am inotriazole two hydrogen atom s in NH_2 in the undoped polym er lie above the plane of the rings, while all the atom s are co-planar in the half-lled poly-am inotriazole. We can more closely look at the torsion angle, , de ned as the angle with which C-N-N-H atom s are connected. Figure 13(b) shows the torsion angles in the P and F states, respectively. From Figs. 13(a) and (b), one can see that the breakdown of the ferrom agnetism with the decrease in the num ber of holes is correlated with the change in the atom ic con guration.

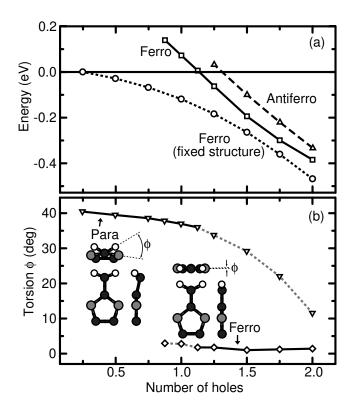


FIG.13: Doping dependence of (a) the total energy (relative to the param agnetic state) of F (solid line), AF (dashed line), and F (xed structure, dotted line, see text) states m easured from that of P state, and (b) torsion angle of C - N - N - H in F (diam onds) and P (reversed triangles) states. Stable states are connected by a solid line, while m etastable states by a dotted line. Insets show front, side, and top views of the atom ic structure of the am inotriazole in P and F states.

W hen the system is half-led ($n_h = 2.0$), all atoms become co-planar, where the N atom of the NH₂ base has sp² hybridized orbitals, forming chemical bonds with two H atoms and a N atom at the top of the ring. The network of the orbitals in poly-am inotriazole is formed by those of the rings and that of NH₂'s. W hen the num - ber of holes is decreased and becomes $n_h < 1.1$, the N atom of the NH₂ forms sp³ hybridized orbitals, i.e., the orbital at NH₂ disappears. Since the chemical bonds

to the N atom and two H atom s are form ed in the three directions of sp^3 , leaving one lone pair, NH₂ has a threedimensional structure. This time, the network consists of ve -orbitals of the rings and a sp^3 hybridized orbital of the lone pair. This change is disadvantageous for the scheme of the at-band formation (Fig. 9) due to the balance of the six orbitals. This is considered why F state always takes a at geometry while P state a non- at geometry.

To see what part of the energy a ects the change in the stable state when $n_{\rm h}$ is decreased, we have calculated the energy di erence between the F and P states by xing the atom ic structure to the optimum one for the F state at $n_{\rm h}$ = 2.0. The result is plotted as a dotted line in F ig. 13 (a). This shows that the value is negative over the whole range plotted here, which indicates that the electronic part of the total energy always favors F state regardless of the lling of the at band. Therefore, the change in the structure, especially of N H_2. If we can nd a material in which there is no such change in the atom ic structure but the parameter values are similar, we can expect an occurrence of the ferrom agnetism even for a low-doping region less than quarter-lling.

In sum m ary, the present work describes an exam ple of m aterials design from rst principles for the purpose of realizing at-band ferrom agnetism in organic polym ers. W e have found a prom ising m aterial, polyam inotriazole, for which why it is the best and the robustness of the ferrom agnetism has been discussed.

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